

212771US-22 PCT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :  
MASASHI KAWASKI ET AL : ATTN: APPLICATION DIVISION  
SERIAL NO: NEW US PCT APPLN :  
(Based on PCT/JP00/01736)  
FILED: HEREWITH : EXAMINER:  
FOR: SEMICONDUCTOR DEVICE :

#L/A  
15 Mar 02  
P. Talley

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 1-10.

Please add new Claims 11-30 as follows:

11. (New) A semiconductor device comprising,  
a substrate containing a material of formula  $\text{LnABO}_4$  or  $\text{LnAO}_3(\text{BO})_n$  for basic  
structure,  
wherein,  
Ln is a rare earth element,  
A is selected from the group consisting of Fe, Ga and Al,  
B is selected from the group consisting of Mn, Co, Fe, Zn, Cu, Mg and Cd,

Al (sub) Bi

09/926186-0110  
2011-09-20